

MOSFETs Silicon Carbide N-Channel MOS

TW107N65C

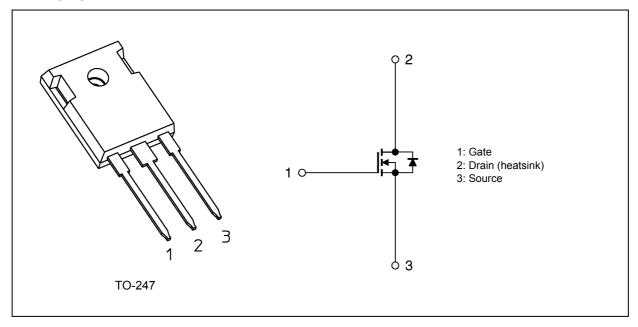
1. Applications

• Switching Voltage Regulators

2. Features

- (1) Chip design of 3rd generation (Built-in SiC schottky barrier diode)
- (2) Low diode forward voltage: $V_{DSF} = -1.35 \text{ V (typ.)}$
- (3) High voltage: $V_{DSS} = 650 \text{ V}$
- (4) Low drain-source on-resistance: $R_{DS(ON)} = 107 \text{ m}\Omega$ (typ.)
- (5) Less susceptible to malfunction due to high threshold voltage: V_{th} = 3.0 to 5.0 V (V_{DS} = 10 V, I_D = 1.2 mA)
- (6) Enhancement mode.

3. Packaging and Internal Circuit





4. Absolute Maximum Ratings (Note) (Unless otherwise specified, T_a = 25 °C)

| | Characteristics | Symbol | Rating | Unit |
|------------------------|----------------------------|------------------|------------|-------|
| Drain-source voltage | | V _{DSS} | 650 | V |
| Gate-source voltage | | V_{GSS} | +25/-10 | |
| Drain current (DC) | (T _c = 25 °C) | I _D | 20 | Α |
| Drain current (DC) | (T _c = 100°C) | I _D | 16 |] |
| Drain current (pulsed) | (T _c = 25 °C) | I _{DP} | 45 | |
| Drain current (pulsed) | (T _c = 100°C) | I _{DP} | 35 |] |
| Power dissipation | (T _c = 25°C) | P _D | 76 | W |
| Channel temperature | | T _{ch} | 175 | ℃ |
| Storage temperature | | T _{stg} | -55 to 175 |] |
| Mounting torque | | TOR | 0.8 | N · m |

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

5. Thermal Characteristics

| Characteristics | | Max | Unit |
|---------------------------------------|-----------------------|-------|------|
| Channel-to-case thermal resistance | R _{th(ch-c)} | 1.950 | °C/W |
| Channel-to-ambient thermal resistance | R _{th(ch-a)} | 50 | |

Note1: Ensure that the channel temperature does not exceed 175 °C.

Caution:This transistor is sensitive to electrostatic discharge and should be handled with care. It should be used for switching applications.



6. Electrical Characteristics

6.1. Static Characteristics (Unless otherwise specified, T_a = 25 °C)

| Characteristics | Symbol | Test Condition | Min | Тур. | Max | Unit |
|--------------------------------|----------------------|--|-----|------|------|------|
| Gate leakage current | I _{GSS} | V _{GS} = +25/-10 V, V _{DS} = 0 V | _ | _ | ±0.1 | μΑ |
| Drain cut-off current | I _{DSS} | V _{DS} = 650 V, V _{GS} = 0 V | _ | 2 | 25 | |
| | | T _a = 150 °C, V _{DS} = 650 V, V _{GS} = 0 V | | 10 | ı | |
| Drain-source breakdown voltage | V _{(BR)DSS} | I _D = 4 mA, V _{GS} = 0 V | 650 | _ | _ | V |
| Gate threshold voltage (Note2 |) V _{th} | V _{DS} = 10 V, I _D = 1.2 mA | 3.0 | _ | 5.0 | |
| Drain-source on-resistance | R _{DS(ON)} | V _{GS} = 18 V, I _D = 10 A | _ | 107 | 145 | mΩ |
| | | T _a = 150 °C, V _{GS} = 18 V, I _D = 10 A | _ | 127 | _ | |

Note2: Please be sure to apply I_{GSS} (V_{GS} = 25 V) before the V_{th} test.

6.2. Dynamic Characteristics (Unless otherwise specified, T_a = 25 °C)

| Characteristics | Symbol | Test Condition | Min | Тур. | Max | Unit |
|--------------------------------|------------------|---|-----|------|-----|------|
| Input capacitance | C _{iss} | V _{DS} = 400 V, V _{GS} = 0 V, | _ | 600 | _ | pF |
| Reverse transfer capacitance | C _{rss} | f = 100 kHz | _ | 3.7 | _ | |
| Output capacitance | C _{oss} |] | | 80 | _ | |
| Output charge | Q _{oss} | | _ | 51 | _ | nC |
| C _{oss} stored energy | E _{oss} | 1 | _ | 7.2 | _ | μJ |
| Gate resistance | r _g | V _{DS} = OPEN, f = 1 MHz | _ | 11 | _ | Ω |
| Switching time (rise time) | t _r | See Fig. 6.2.1 | _ | 32 | _ | ns |
| Switching time (turn-on time) | t _{on} | 1 | _ | 56 | _ | |
| Switching time (fall time) | t _f | 1 | _ | 25 | _ | |
| Switching time (turn-off time) | t _{off} |] | _ | 56 | _ | |

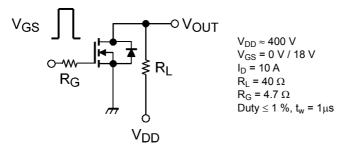


Fig. 6.2.1 Switching Time Test Circuit

6.3. Gate Charge Characteristics (Unless otherwise specified, T_a = 25 °C)

| Characteristics | Symbol | Test Condition | Min | Тур. | Max | Unit |
|---|------------------|--|-----|------|-----|------|
| Total gate charge (gate-source plus gate-drain) | | $V_{DD} \approx 400 \text{ V}, V_{GS} = 18 \text{ V},$ $I_{D} = 10 \text{ A}$ | 1 | 21 | ı | nC |
| Gate-source charge 1 | Q _{gs1} | | _ | 12 | _ | |
| Gate-drain charge | Q_{gd} | | _ | 2.3 | _ | |



6.4. Source-Drain Characteristics (Unless otherwise specified, T_a = 25 °C)

| Characteristics | | Symbol | Test Condition | Min | Тур. | Max | Unit |
|-------------------------------|---------|------------------|---|-----|-------|-------|------|
| Reverse drain current (DC) | (Note3) | I _{DR} | T _c = 25 °C, V _{GS} = -5 V | _ | _ | 18 | Α |
| | | | T _c = 100 °C, V _{GS} = -5 V | _ | _ | 12 | |
| | | | T _c = 25 °C, V _{GS} = 18 V | _ | _ | 20 | |
| | | | T _c = 100 °C, V _{GS} = 18 V | _ | _ | 16 | |
| Reverse drain current | (Note3) | I _{DRP} | T _c = 25 °C, V _{GS} = -5 V | _ | _ | 45 | |
| (pulsed) | | | T _c = 100 °C, V _{GS} = -5 V | _ | _ | 27 | |
| | | | T _c = 25 °C, V _{GS} = 18 V | _ | _ | 45 | |
| | | | T _c = 100 °C, V _{GS} = 18 V | _ | _ | 35 | |
| Diode forward voltage | | V _{DSF} | I _{DR} = 5 A, V _{GS} = -5 V | _ | -1.35 | -1.80 | V |
| | | | T _a = 150 °C, I _{DR} = 5 A, V _{GS} = -5 V | _ | -1.60 | _ | |
| Reverse recovery time | | t _{rr} | I _{DR} = 7 A, V _{GS} = 0 V, | _ | 38 | _ | ns |
| Reverse recovery charge | | Q _{rr} | $V_{DD} = 400 \text{ V}, -dI_{DR}/dt = 1000 \text{ A}/\mu\text{s}$ | _ | 137 | _ | nC |
| Peak reverse recovery current | | I _{rr} | | _ | 7.2 | _ | А |

Note3: Ensure that the channel temperature does not exceed 175 $^{\circ}\text{C}$.

Rev.1.0



7. Marking (Note)

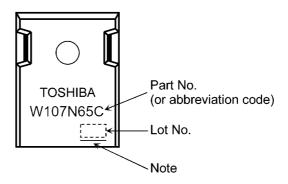


Fig. 7.1 Marking

Note: A line under a Lot No. identifies the indication of product Labels.

Not underlined: [[Pb]]/INCLUDES > MCV

Underlined: [[G]]/RoHS COMPATIBLE or [[G]]/RoHS [[Pb]]

Please contact your TOSHIBA sales representative for details as to environmental matters such as the RoHS compatibility of Product.

The RoHS is the Directive 2011/65/EU of the European Parliament and of the Council of 8 June 2011 on the

restriction of the use of certain hazardous substances in electrical and electronic equipment.



8. Characteristics Curves (Note)

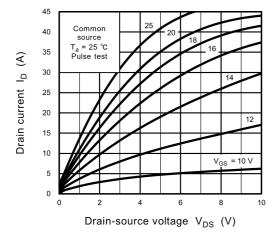


Fig. 8.1 I_D - V_{DS}

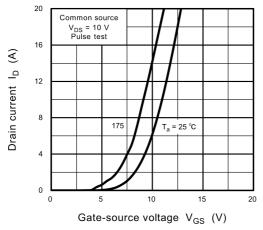


Fig. 8.3 I_D - V_{GS}

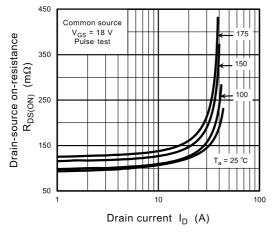


Fig. 8.5 R_{DS(ON)} - I_D

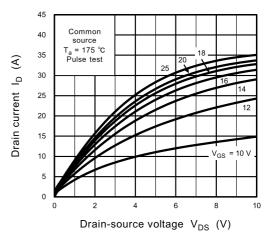


Fig. 8.2 I_D - V_{DS}

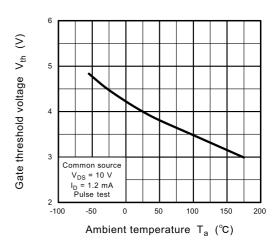


Fig. 8.4 V_{th} - T_a

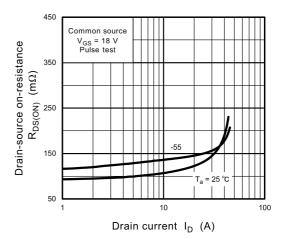


Fig. 8.6 R_{DS(ON)} - I_D



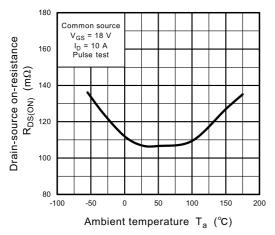


Fig. 8.7 R_{DS(ON)} - T_a

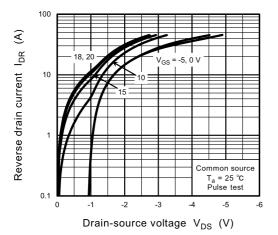


Fig. 8.9 IDR - VDS

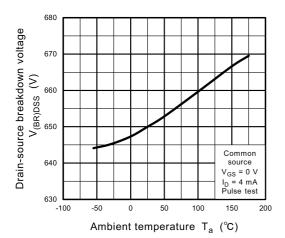


Fig. 8.11 V_{DSS} - T_a

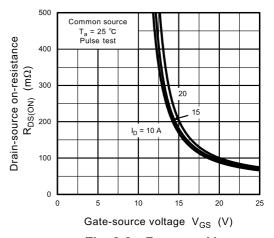


Fig. 8.8 R_{DS(ON)} - V_{GS}

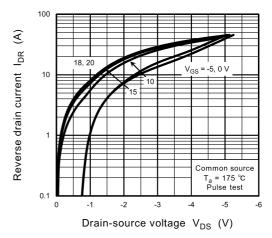


Fig. 8.10 I_{DR} - V_{DS}

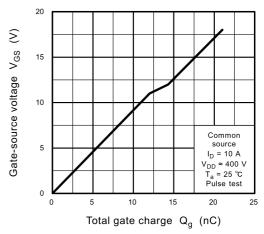
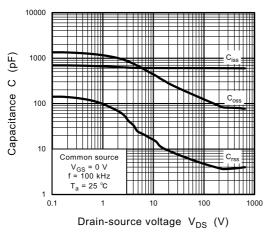


Fig. 8.12 Dynamic Input Characteristics





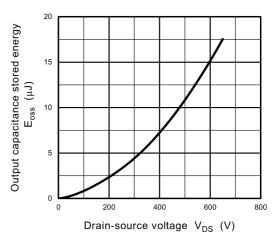
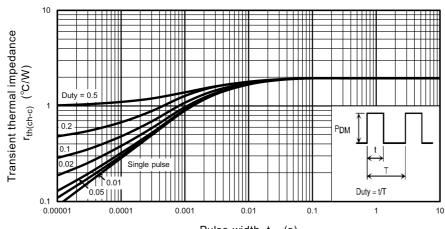


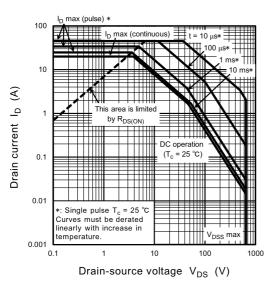
Fig. 8.13 C - V_{DS}

Fig. 8.14 E_{oss} - V_{DS}



Pulse width t_w (s)

Fig. 8.15 $r_{th(ch-c)} - t_w$ (Guaranteed Maximum)



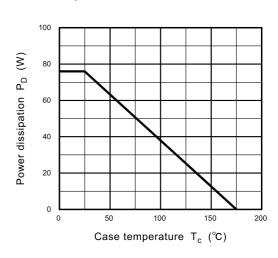


Fig. 8.16 Safe Operating Area (Guaranteed Maximum)

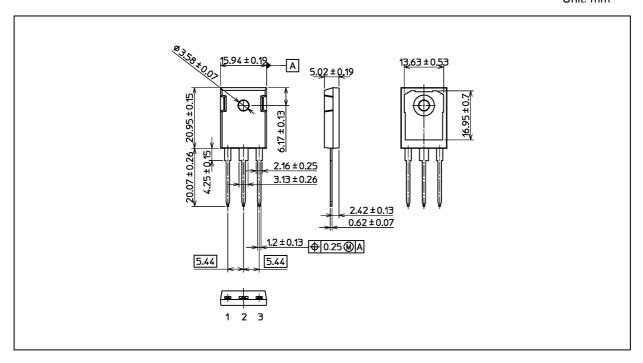
Fig. 8.17 P_D - T_c (Guaranteed Maximum)

Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.



Package Dimensions

Unit: mm



Weight: 6.15 g (typ.)

| Package Name(s) |
|------------------|
| TOSHIBA: 2-16L1A |
| Nickname: TO-247 |



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